

2N6344A, 2N6348A, 2N6349A

Preferred Device

Triacs

Silicon Bidirectional Thyristors

Designed primarily for full-wave ac control applications, such as light dimmers, motor controls, heating controls and power supplies; or wherever full-wave silicon gate controlled solid-state devices are needed. Triac type thyristors switch from a blocking to a conducting state for either polarity of applied anode voltage with positive or negative gate triggering.

- Blocking Voltage to 800 Volts
- All Diffused and Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Gate Triggering Guaranteed in all Four Quadrants
- For 400 Hz Operation, Consult Factory
- 8 Ampere Devices Available as 2N6344 thru 2N6349
- Device Marking: Logo, Device Type, e.g., 2N6344A, Date Code

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
*Peak Repetitive Off-State Voltage ⁽¹⁾ (Gate Open, $T_J = -40$ to $+110^\circ\text{C}$, Sine Wave 50 to 60 Hz, Gate Open) 2N6344A, 2N6348A 2N6349A	V_{DRM} , V_{RRM}	600 800	Volts
*On-State RMS Current (Full Cycle Sine Wave 50 to 60 Hz) ($T_C = +80^\circ\text{C}$) ($T_C = +95^\circ\text{C}$)	$I_T(\text{RMS})$	12 6.0	A
*Peak Non-repetitive Surge Current (One Full Cycle, 60 Hz, $T_C = +80^\circ\text{C}$) Preceded and followed by rated current	I_{TSM}	100	A
Circuit Fusing Consideration ($t = 8.3$ ms)	I^2t	59	A^2s
*Peak Gate Power ($T_C = +80^\circ\text{C}$, Pulse Width = 2.0 μs)	P_{GM}	20	Watts
*Average Gate Power ($T_C = +80^\circ\text{C}$, $t = 8.3$ ms)	$P_{G(AV)}$	0.5	Watt
*Peak Gate Current (Pulse Width = 2.0 μs ; $T_C = +80^\circ\text{C}$)	I_{GM}	2.0	A
*Peak Gate Voltage (Pulse Width = 2.0 μs ; $T_C = +80^\circ\text{C}$)	V_{GM}	± 10	Volts
*Operating Junction Temperature Range	T_J	-40 to $+125$	$^\circ\text{C}$
*Storage Temperature Range	T_{stg}	-40 to $+150$	$^\circ\text{C}$

*Indicates JEDEC Registered Data.

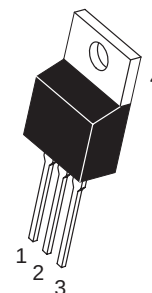
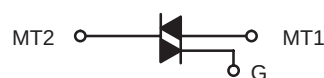
(1) V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



ON Semiconductor

<http://onsemi.com>

TRIACS
12 AMPERES RMS
600 thru 800 VOLTS



TO-220AB
CASE 221A
STYLE 4

PIN ASSIGNMENT

1	Main Terminal 1
2	Main Terminal 2
3	Gate
4	Main Terminal 2

ORDERING INFORMATION

Device	Package	Shipping
2N6344A	TO220AB	500/Box
2N6348A	TO220AB	500/Box
2N6349A	TO220AB	500/Box

Preferred devices are recommended choices for future use and best overall value.

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THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
*Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.0	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	T_L	260	°C

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted; Electricals apply in either direction)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

*Peak Repetitive Blocking Current ($V_D = \text{Rated } V_{DRM}, V_{RRM}; \text{ Gate Open}$)	I_{DRM}, I_{RRM}	—	—	10	μA
$T_J = 25^\circ\text{C}$ $T_J = 110^\circ\text{C}$		—	—	2.0	mA

ON CHARACTERISTICS

*Peak On-State Voltage ($I_{TM} = \pm 17 \text{ A Peak}; \text{ Pulse Width} = 1 \text{ to } 2 \text{ ms}, \text{ Duty Cycle} \leq 2\%$)	V_{TM}	—	1.3	1.75	Volts
Gate Trigger Current (Continuous dc) ($V_D = 12 \text{ Vdc}, R_L = 100 \text{ Ohms}$) MT2(+), G(+) MT2(+), G(–) MT2(–), G(–) MT2(–), G(+) *MT2(+), G(+); MT2(–), G(–) $T_C = -40^\circ\text{C}$ *MT2(+), G(–); MT2(–), G(+), $T_C = -40^\circ\text{C}$	I_{GT}	— — — — —	6.0 6.0 10 25	50 75 50 75	mA
Gate Trigger Voltage (Continuous dc) ($V_D = 12 \text{ Vdc}, R_L = 100 \text{ ohms}$) MT2(+), G(+) MT2(+), G(–) MT2(–), G(–) MT2(–), G(+) *MT2(+), G(+); MT2(–), G(–) $T_C = -40^\circ\text{C}$ *MT2(+), G(–); MT2(–), G(+), $T_C = -40^\circ\text{C}$	V_{GT}	— — — —	0.9 0.9 1.1 1.4	2.0 2.5 2.0 2.5	Volts
Gate Non-Trigger Voltage ($V_D = \text{Rated } V_{DRM}, R_L = 10 \text{ k ohms}, T_J = 110^\circ\text{C}$) *MT2(+), G(+); MT2(–), G(–); MT2(+), G(–); MT2(–), G(+)	V_{GD}	0.2	—	—	Volts
Holding Current ($V_D = 12 \text{ Vdc}, \text{ Gate Open}$) Initiating Current = $\pm 200 \text{ mA}$	I_H	— —	6.0 —	40 75	mA
$T_C = 25^\circ\text{C}$ $*T_C = -40^\circ\text{C}$					
*Turn-On Time ($V_D = \text{Rated } V_{DRM}, I_{TM} = 17 \text{ A}, I_{GT} = 120 \text{ mA},$ Rise Time = $0.1 \mu\text{s}$, Pulse Width = $2 \mu\text{s}$)	t_{gt}	—	1.5	2.0	μs

DYNAMIC CHARACTERISTICS

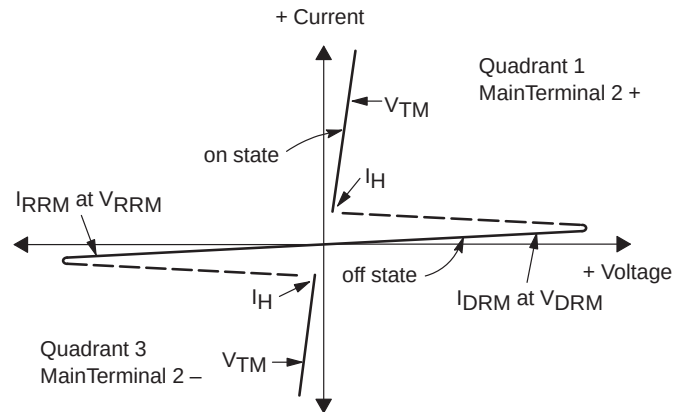
Critical Rate of Rise of Commutation Voltage ($V_D = \text{Rated } V_{DRM}, I_{TM} = 17 \text{ A}, \text{ Commutating } di/dt = 6.1 \text{ A/ms},$ Gate Unenergized, $T_C = 80^\circ\text{C}$)	$dv/dt(c)$	—	5.0	—	V/ μs
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*Indicates JEDEC Registered Data.

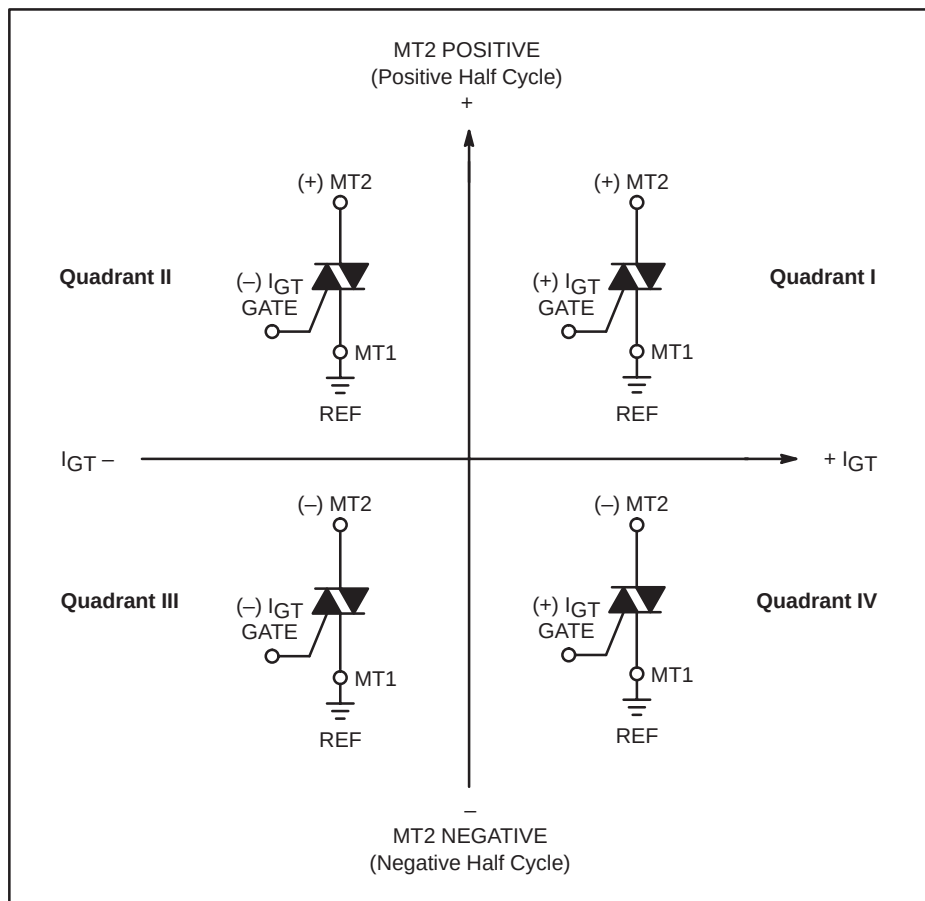
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Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
V_{DRM}	Peak Repetitive Forward Off State Voltage
I_{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Reverse Off State Voltage
I_{RRM}	Peak Reverse Blocking Current
V_{TM}	Maximum On State Voltage
I_H	Holding Current



Quadrant Definitions for a Triac



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.

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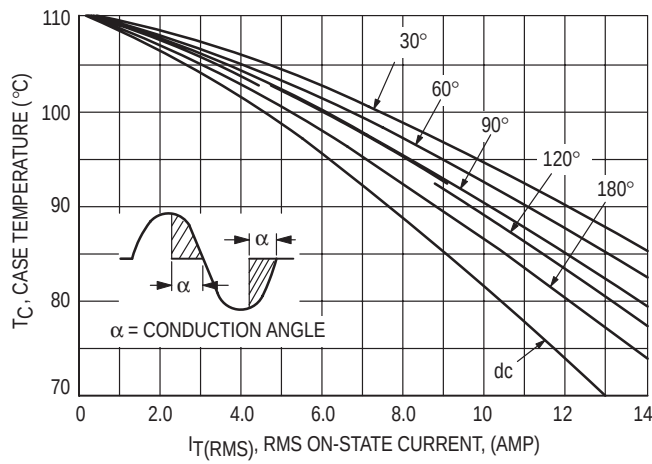


Figure 1. RMS Current Derating

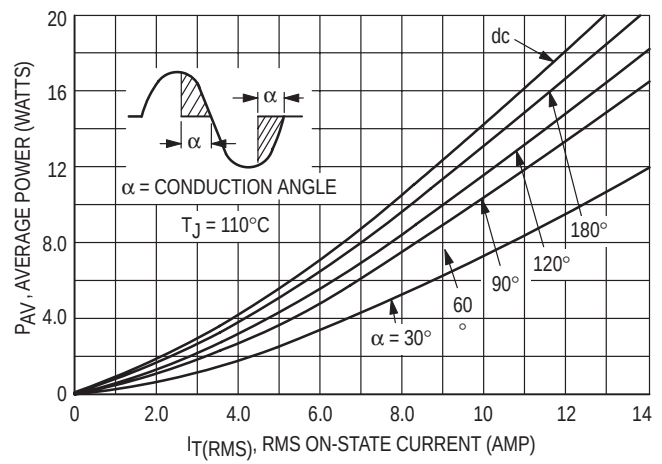


Figure 2. On-State Power Dissipation

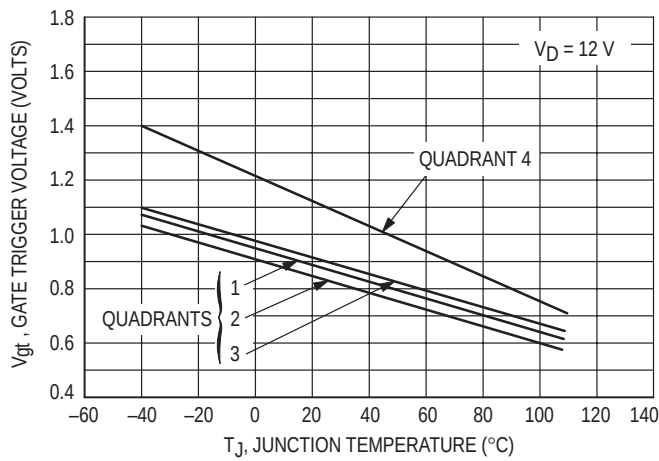


Figure 3. Typical Gate Trigger Voltage

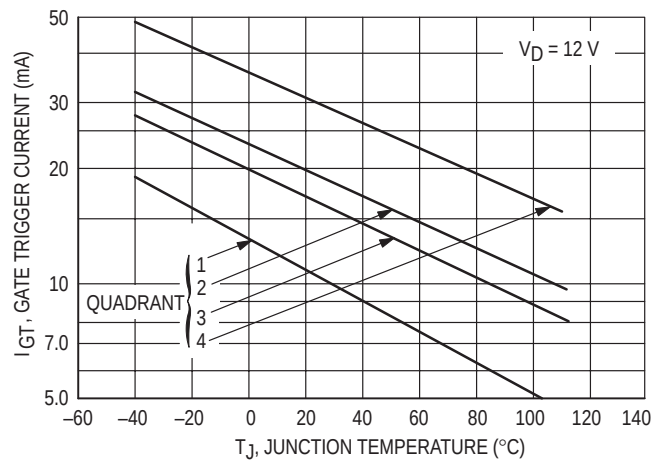


Figure 4. Typical Gate Trigger Current

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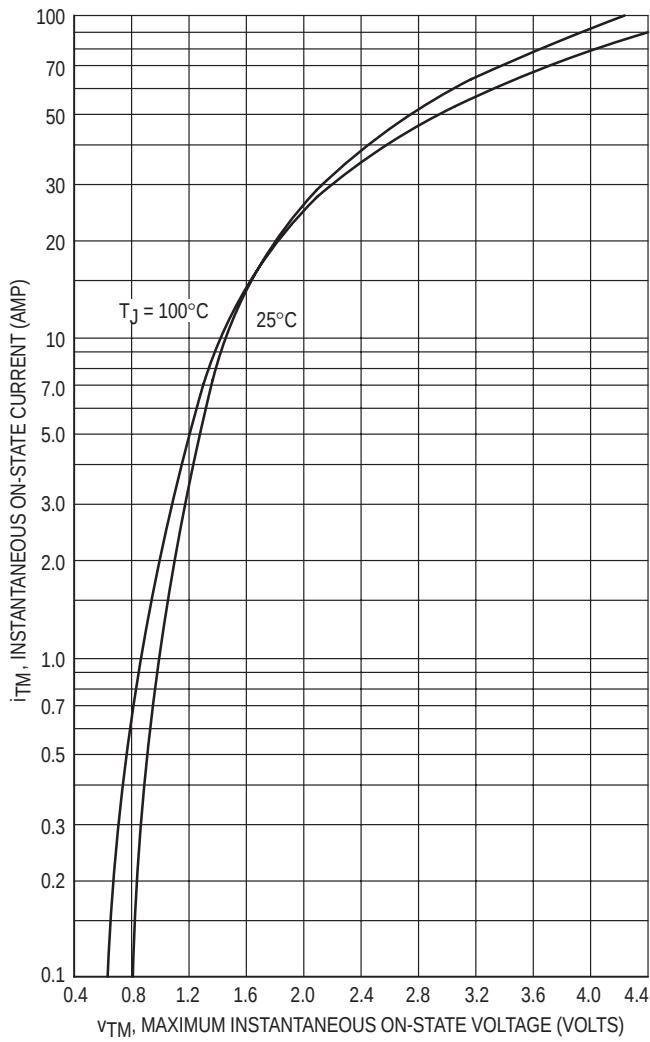


Figure 5. On-State Characteristics

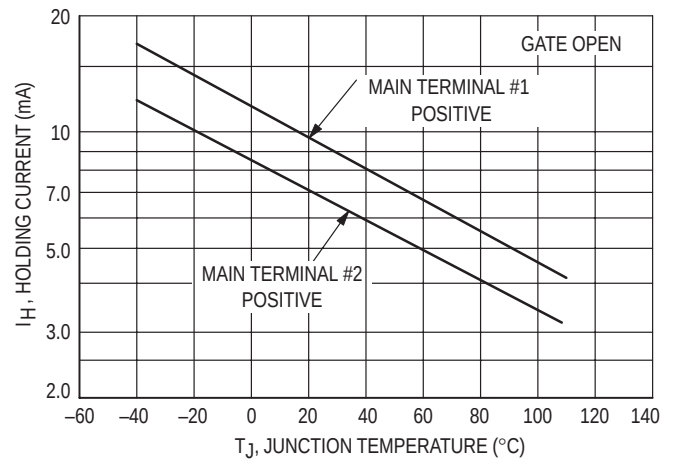


Figure 6. Typical Holding Current

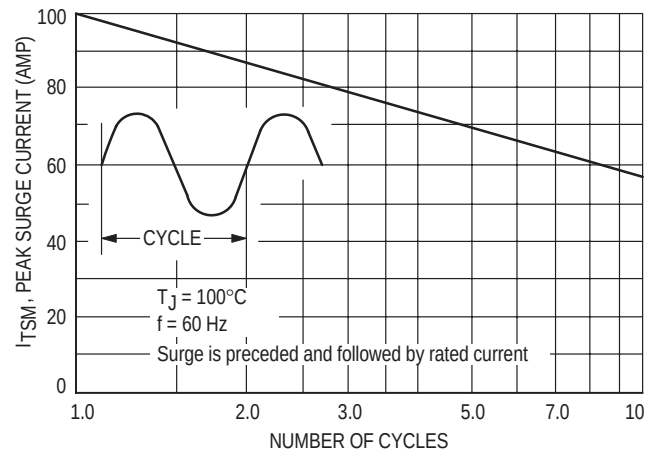


Figure 7. Maximum Non-Repetitive Surge Current

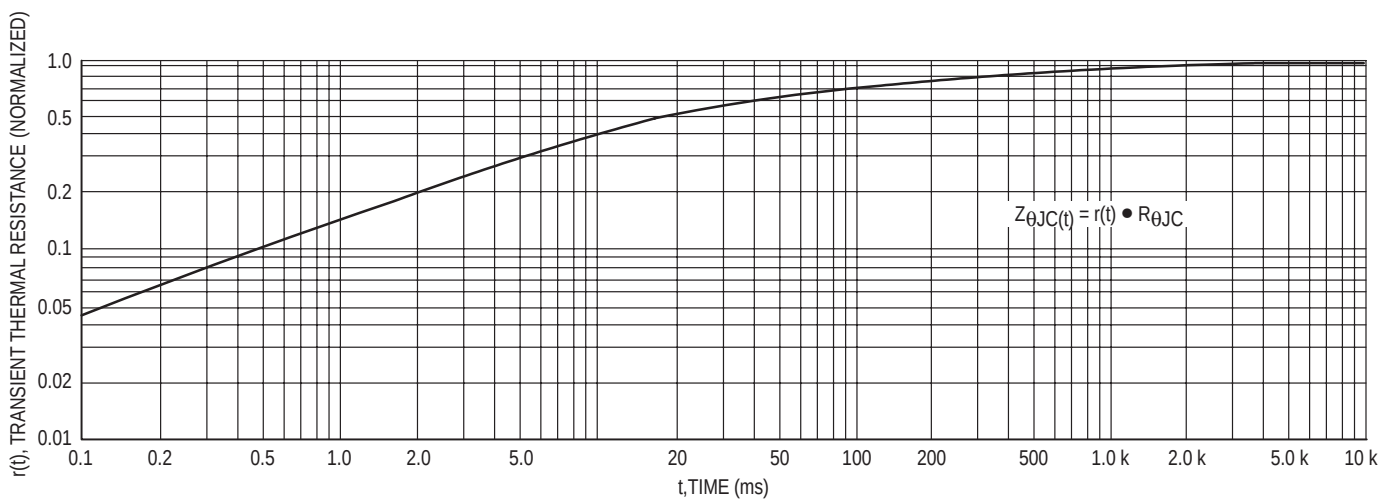
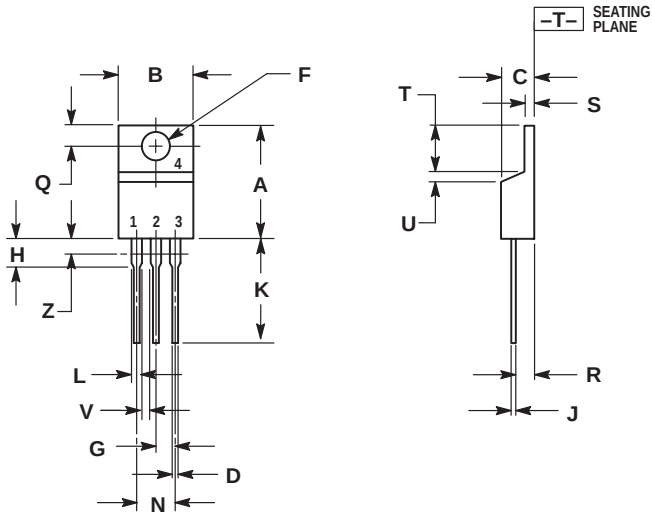


Figure 8. Typical Thermal Response

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PACKAGE DIMENSIONS

TO-220AB CASE 221A-07 ISSUE Z



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.014	0.022	0.36	0.55
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
O	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	—	1.15	—
Z	—	0.080	—	2.04

STYLE 4:

- PIN 1. MAIN TERMINAL 1
- MAIN TERMINAL 2
- GATE
- MAIN TERMINAL 2

Notes

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